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November 2013

### FGH25N120FTDS 1200 V, 25 A Field Stop Trench IGBT

#### **Features**

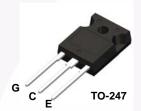
- High Speed Switching
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.60 V @ I<sub>C</sub> = 25 A
- High Input Impedance
- RoHS Compliant

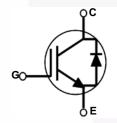
#### **Applications**

· Solar Inverter, UPS, Welder, PFC

### **General Description**

Using advanced field stop trench technology, Fairchild's 1200V trench IGBTs offer the optimum performance for hard switching application such as solar inverter, UPS, welder and PFC applications.





### **Absolute Maximum Ratings**

| Symbol              | Description   |                         | Ratings     | Unit |
|---------------------|---|-------------------------|-------------|------|
| V <sub>CES</sub>    | Collector to Emitter Voltage  |                         | 1200        | V    |
| V <sub>GES</sub>    | Gate to Emitter Voltage   |                         | ± 25        | V    |
| I <sub>C</sub>      | Collector Current   | $@ T_C = 25^{\circ}C$   | 50          | А    |
|                     | Collector Current   | $@ T_C = 100^{\circ}C$  | 25          | Α    |
| I <sub>CM (1)</sub> | Pulsed Collector Current  |                         | 75          | Α    |
|                     | Diode Continuous Forward Current  | @ T <sub>C</sub> = 25°C | 50          | A    |
| <sup>1</sup> F      | Diode Continuous Forward Current @ T <sub>C</sub> = 100°C               |                         | 25          | A    |
| I <sub>FM</sub>     | Diode Maximum Forward Current   |                         | 75          | A    |
| P <sub>D</sub>      | Maximum Power Dissipation   | @ T <sub>C</sub> = 25°C | 313         | W    |
| ' Б                 | Maximum Power Dissipation @ T <sub>C</sub> = 100°C                      |                         | 125         | W    |
| T <sub>J</sub>      | Operating Junction Temperature  |                         | -55 to +150 | °C   |
| T <sub>stg</sub>    | Storage Temperature Range   |                         | -55 to +150 | °C   |
| T <sub>L</sub>      | Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds |                         | 300         | °C   |

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

#### **Thermal Characteristics**

| Symbol                 | Parameter                                    | Тур. | Max. | Unit |
|------------------------|--|------|------|------|
| $R_{\theta JC}(IGBT)$  | C(IGBT) Thermal Resistance, Junction to Case |      | 0.4  | °C/W |
| $R_{\theta JC}(Diode)$ | Thermal Resistance, Junction to Case         | -    | 1.25 | °C/W |
| $R_{\theta JA}$        | Thermal Resistance, Junction to Ambient      | -    | 40   | °C/W |

### **Package Marking and Ordering Information**

| Part Number   | Top Mark      | Package | Packing Method | Reel Size | Tape Width | Quantity |
|---------------|---------------|---------|----------------|-----------|------------|----------|
| FGH25N120FTDS | FGH25N120FTDS | TO-247  | Tube           | N/A       | N/A        | 30       |

### Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

| Symbol               | Parameter                               | Test Conditions  | Min. | Тур. | Max. | Unit |
|----------------------|---|--|------|------|------|------|
| Off Charac           | teristics                               |  |      |      |      |      |
| BV <sub>CES</sub>    | Collector to Emitter Breakdown Voltage  | $V_{GE} = 0 \text{ V}, I_{C} = 250 \mu A$  | 1200 | -    | -    | V    |
| I <sub>CES</sub>     | Collector Cut-Off Current               | $V_{CE} = V_{CES}$ , $V_{GE} = 0$ V  | -    | -    | 1    | mA   |
| I <sub>GES</sub>     | G-E Leakage Current                     | $V_{GE} = V_{GES}, V_{CE} = 0 V$   | -    | -    | ±250 | nA   |
| On Charac            | teristics                               |  |      |      |      |      |
| V <sub>GE(th)</sub>  | G-E Threshold Voltage                   | I <sub>C</sub> = 25 mA, V <sub>CE</sub> = V <sub>GE</sub>  | 3.5  | 6    | 7.5  | V    |
|                      |   | I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V  | -    | 1.6  | 2    | V    |
| V <sub>CE(sat)</sub> | Collector to Emitter Saturation Voltage | $I_C = 25 \text{ A}, V_{GE} = 15 \text{ V},$<br>$T_C = 125^{\circ}\text{C}$  | -    | 1.92 | -    | V    |
| Dynamic C            | haracteristics                          |  |      | 1    |      |      |
| C <sub>ies</sub>     | Input Capacitance                       |  | -    | 4090 | -    | pF   |
| C <sub>oes</sub>     | Output Capacitance                      | $V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$<br>f = 1  MHz   | -    | 135  | -    | pF   |
| C <sub>res</sub>     | Reverse Transfer Capacitance            | - I = I WIMZ   | -    | 75   | -    | pF   |
| Switching            | Characteristics                         |  |      |      |      |      |
| t <sub>d(on)</sub>   | Turn-On Delay Time                      | $V_{CC} = 600 \text{ V}, I_{C} = 25 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ Inductive Load, $T_{C} = 25^{\circ}\text{C}$ | -    | 26   | 35   | ns   |
| t <sub>r</sub>       | Rise Time                               |  | -    | 41   | 53   | ns   |
| t <sub>d(off)</sub>  | Turn-Off Delay Time                     |  | -    | 151  | 196  | ns   |
| t <sub>f</sub>       | Fall Time                               |  | -    | 102  | 132  | ns   |
| E <sub>on</sub>      | Turn-On Switching Loss                  |  | -    | 1.42 | 1.84 | mJ   |
| E <sub>off</sub>     | Turn-Off Switching Loss                 |  | -    | 1.16 | 1.5  | mJ   |
| E <sub>ts</sub>      | Total Switching Loss                    |  | -    | 2.58 | 3.34 | mJ   |
| t <sub>d(on)</sub>   | Turn-On Delay Time                      |  | - /  | 22   | -    | ns   |
| t <sub>r</sub>       | Rise Time                               |  | -    | 41   | -    | ns   |
| t <sub>d(off)</sub>  | Turn-Off Delay Time                     | $V_{CC} = 600 \text{ V}, I_{C} = 25 \text{ A},$  | -    | 163  | -    | ns   |
| t <sub>f</sub>       | Fall Time                               | $R_G = 10 \Omega$ , $V_{GE} = 15 V$ ,  | -    | 136  | =    | ns   |
| E <sub>on</sub>      | Turn-On Switching Loss                  | Inductive Load, T <sub>C</sub> = 125°C   | -    | 2.04 | -    | mJ   |
| E <sub>off</sub>     | Turn-Off Switching Loss                 |  | -    | 1.58 | -    | mJ   |
| E <sub>ts</sub>      | Total Switching Loss                    |  | -    | 3.62 | - // | mJ   |
| Qg                   | Total Gate Charge                       |  | -    | 169  | 225  | nC   |
| Q <sub>ge</sub>      | Gate to Emitter Charge                  | $V_{CE} = 600 \text{ V}, I_{C} = 25 \text{ A},$<br>$V_{GE} = 15 \text{ V}$   | -    | 33   | 44   | nC   |
| Q <sub>gc</sub>      | Gate to Collector Charge                | ▼GE - 13 V   | -    | 78   | 104  | nC   |

### Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol                                    | Parameter                            | Test Conditions         |                                  | Min. | Тур. | Max  | Unit |
|---|--------------------------------------|-------------------------|----------------------------------|------|------|------|------|
| V <sub>FM</sub>                           | Diode Forward Voltage                | I <sub>F</sub> = 25 A   | $T_{\rm C} = 25^{\rm o}{\rm C}$  | -    | 2.5  | 3.5  | V    |
|   |                                      |                         | $T_{\rm C} = 125^{\rm o}{\rm C}$ | -    | 2.3  | -    |      |
| t <sub>rr</sub>                           | Diode Reverse Recovery Time          |                         | $T_C = 25^{\circ}C$              | -    | 411  | 535  | ns   |
|   | ·                                    | I <sub>F</sub> = 25 A,  | $T_{\rm C} = 125^{\rm o}{\rm C}$ | -    | 496  | -    |      |
| I   | Diode Peak Reverse Recovery Current  | $di_F/dt = 200 A/\mu s$ | $T_C = 25^{\circ}C$              | -    | 5.2  | 6.8  | Α    |
| ı <sub>rr</sub>                           | Disact can revolve reservely carrein |                         | $T_{\rm C} = 125^{\rm o}{\rm C}$ | -    | 6.9  | -    | ]    |
| Q <sub>rr</sub> Diode Reverse Recovery Ch | Diode Reverse Recovery Charge        |                         | $T_{\rm C} = 25^{\rm o}{\rm C}$  | -    | 1.1  | 1.82 | μС   |
|   |                                      |                         | $T_{\rm C} = 125^{\rm o}{\rm C}$ | -    | 1.7  | -    |      |

Figure 1. Typical Output Characteristics

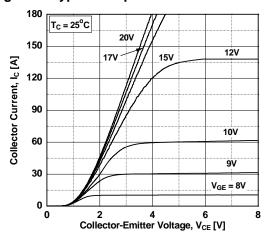


Figure 3. Typical Saturation Voltage Characteristics

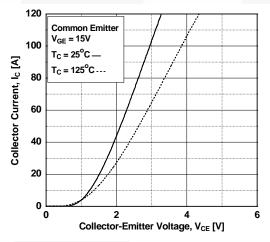
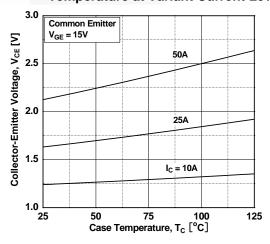


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 

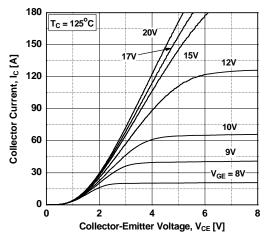


Figure 4. Transfer Characteristics

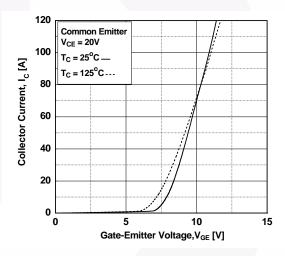


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

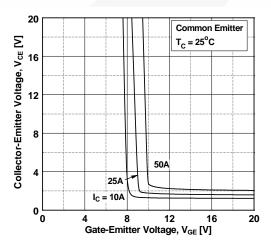


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

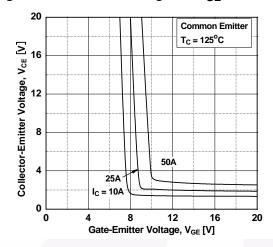


Figure 8. Load Current vs. Frequency

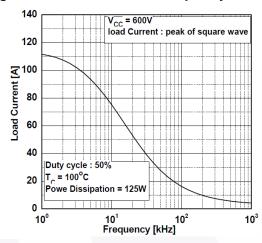


Figure 9. Capacitance Characteristics

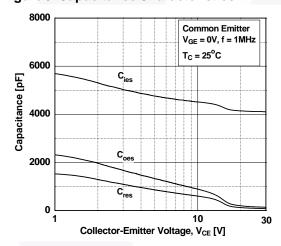


Figure 10. Gate Charge Characteristics

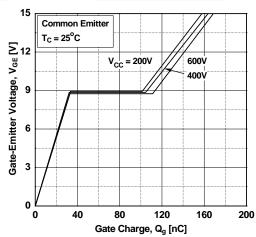


Figure 11. SOA Characteristics
Gate Resistance

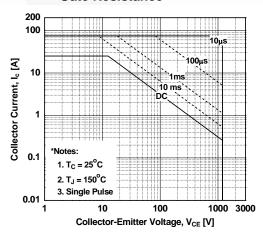


Figure 12. Turn-on Characteristics vs.
Gate Resistance

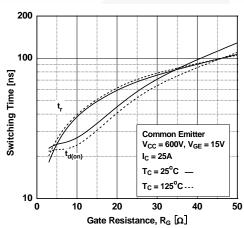


Figure 13. Turn-off Characteristics vs.
Gate Resistance

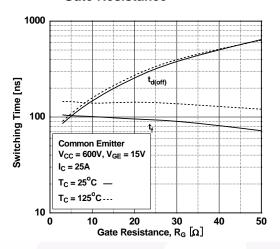


Figure 15. Turn-off Characteristics vs. Collector Current

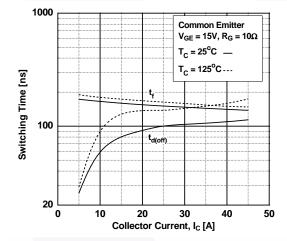


Figure 17. Switching Loss vs. Collector Current

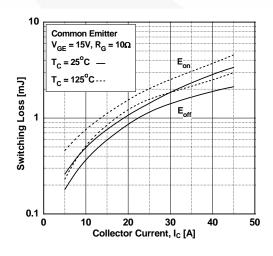


Figure 14. Turn-on Characteristics vs. Collector Current

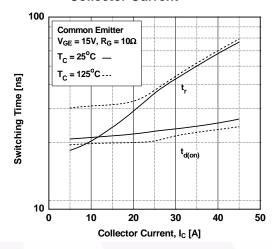


Figure 16. Switching Loss vs. Gate Resistance

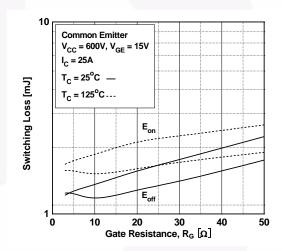


Figure 18. Turn off Switing SOA Characteristics

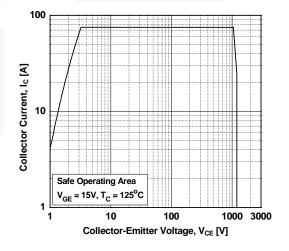


Figure 19. Forward Characteristics

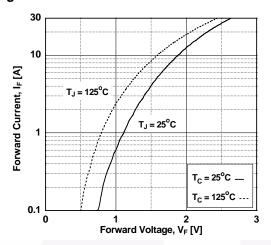


Figure 20. Reverse Recovery Current

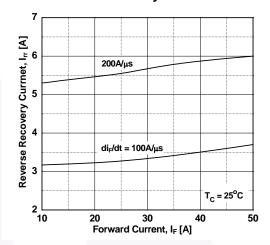


Figure 21. Stored Charge

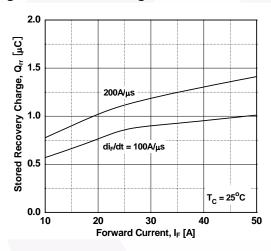


Figure 22. Reverse Recovery Time

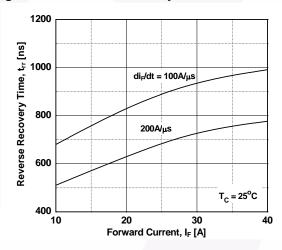
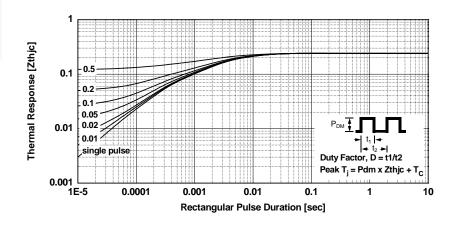


Figure 23. Transient Thermal Impedance of IGBT



## **Mechanical Dimensions** В 15.87 E φ<sup>3.65</sup>/<sub>3.51</sub>/<sub>E</sub> Φ 0.254 Μ Β ΑΜ 12.81 E $\phi_{3.51}^{3.65}$ 5.58 E 1.35 Ø 5.20 F 13.08 MIN 3 16.25 E (1.60) 3 2.66 5.56 1.17 0.254 M B AM 11.12 NOTES: UNLESS OTHERWISE SPECIFIED. A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004. B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS. ALL DIMENSIONS ARE IN MILLIMETERS. D. DRAWING CONFORMS TO ASME Y14.5 - 1994 DOES NOT COMPLY JEDEC STANDARD VALUE

Figure 24. TO-247 3L - TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

#### Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001:
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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